

Abstract

A semiconductor device including a resistive conductive layer and a method of manufacturing the semiconductor device.

A method of manufacturing a semiconductor device in which a resistive conductive layer and an MOS transistor are provided on the same semiconductor layer in a mixed manner. The method comprises the steps of forming a resistive conductive layer on the first insulating layer in a formation region for the resistive conductive layer; forming a protective layer so as to cover the resistive conductive layer; and forming a gate insulating layer and a gate electrode in a formation region for the MOS transistor.

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